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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF:

:GROUP ART UNIT: 1775

RAVINDRANATH DROOPAD ET AL

:

SERIAL NO.: 09/901,109

:EXAMINER: STEIN, S.J.

FILED: JULY 10, 2001

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FOR: STRUCTURE AND METHOD FOR FABRICATING SEMICONDUCTOR
STRUCTURE AND DEVICES UTILIZING THE FORMATION OF A
COMPLIANT SUBSTRATE COMPRISING AN OXYGEN-DOPED COMPOUND
SEMICONDUCTOR LAYER

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

RECEIVED
OCT 21 2002
TC 1700 MAIL ROOM

Responsive to the Official Action dated July 18, 2002, Applicants request
reconsideration in view of the following amendments and remarks.

Please amend the claims to read as follows:

Q1
--4. The semiconductor structure of claim 2, wherein said monocrystalline material layer comprises a material selected from the group consisting of Group III-V compound semiconductors, mixed III-V compounds, Group II-VI compound semiconductors, mixed II-VI compounds, Group IV-VI compound semiconductors, and mixed IV-VI compounds.

5. The semiconductor structure of claim 2, wherein said monocrystalline material layer comprises a material selected from the group consisting of gallium arsenide, gallium indium arsenide, gallium aluminum arsenide, indium phosphide, cadmium sulfide, cadmium mercury telluride, zinc selenide, zinc sulfur selenide, lead selenide, lead telluride, and lead sulfide selenide.